

Gabriel Ferro

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

158
papers

1,401
citations

21
h-index

31
g-index

174
ext. papers

1,533
ext. citations

1.7
avg, IF

4.34
L-index

#	Paper	IF	Citations
158	Growth and Characterization of Undoped Polysilicon Thick Layers: Revisiting an Old System. <i>Silicon</i> , 2020 , 12, 1187-1194	2.4	1
157	How to Grow Fully (100) Oriented SiC/Si/SiC/Si Multi-Stack. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1800588	1.6	
156	Nanodiamond Integration with Photonic Devices. <i>Laser and Photonics Reviews</i> , 2019 , 13, 1800316	8.3	32
155	Two-dimensional defect mapping of the SiO ₂ /4H-SiC interface. <i>Physical Review Materials</i> , 2019 , 3,	3.2	9
154	Understanding Al incorporation into 4H-SiC during epitaxy. <i>Journal of Crystal Growth</i> , 2019 , 507, 338-343	1.6	3
153	The (001) 3C SiC surface termination and band structure after common wet chemical etching procedures, stated by XPS, LEED, and HREELS. <i>Applied Surface Science</i> , 2018 , 427, 480-485	6.7	14
152	Silicon (001) Heteroepitaxy on 3C-SiC(001)/Si(001) Seed. <i>Materials Science Forum</i> , 2018 , 924, 128-131	0.4	
151	A new model for in situ nitrogen incorporation into 4H-SiC during epitaxy. <i>Scientific Reports</i> , 2017 , 7, 43069	4.9	13
150	Silicon Deposition on 3C-SiC Seeds of Different Orientations. <i>Materials Science Forum</i> , 2017 , 897, 87-90	0.4	3
149	Analysis of 4H-SiC MOS Capacitors on Macro-Stepped Surfaces. <i>Materials Science Forum</i> , 2017 , 897, 107-110	0.4	2
148	Low temperature homoepitaxy of GaN structures by Vapor Liquid Solid transport. <i>Journal of Crystal Growth</i> , 2017 , 467, 18-28	1.6	0
147	Growth of aluminum nitride on flat and patterned Si (111) by high temperature halide CVD. <i>Thin Solid Films</i> , 2017 , 623, 65-71	2.2	3
146	Very High Sustainable Forward Current Densities on 4H-SiC p-n Junctions Formed by VLS Localized Epitaxy of Heavily Al-Doped p++ Emitters. <i>Materials Science Forum</i> , 2017 , 897, 63-66	0.4	0
145	Highly Mg-doped GaN dots and films grown by VLS transport at low temperature. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600428	1.6	2
144	Optimization of VLS Growth Process for 4H-SiC P/N Junctions. <i>Materials Science Forum</i> , 2016 , 858, 205-208	0.4	2
143	Thermally Stable Ohmic Contact to p-Type 4H-SiC Based on Ti ₃ SiC ₂ Phase. <i>Materials Science Forum</i> , 2016 , 858, 553-556	0.4	
142	A Study on the Temperature of Ohmic Contact to p-Type SiC Based on Ti ₃ SiC ₂ Phase. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2462-2468	2.9	22

141	Hybrid Group IV Nanophotonic Structures Incorporating Diamond Silicon-Vacancy Color Centers. <i>Nano Letters</i> , 2016 , 16, 212-7	11.5	35
140	3C-SiC Microdisks for Visible Photonics. <i>Materials Science Forum</i> , 2016 , 858, 711-714	0.4	
139	Optimization of the Silicidation and Growth Processes for 3C-SiC Heteroepitaxy on Diamond Substrate. <i>Materials Science Forum</i> , 2016 , 858, 155-158	0.4	1
138	4H-SiC(0001) Surface Faceting during Interaction with Liquid Si. <i>Materials Science Forum</i> , 2016 , 858, 163-166	0.4	2
137	VLS Grown 4H-SiC Buried P+ Layers for JFET Lateral Structures. <i>Materials Science Forum</i> , 2015 , 821-823, 789-792	0.4	1
136	On the Formation of Graphene by Ge Intercalation of a 4H-SiC Surface. <i>Materials Science Forum</i> , 2015 , 821-823, 961-964	0.4	2
135	Evidence for Flat Bands near the Fermi Level in Epitaxial Rhombohedral Multilayer Graphene. <i>ACS Nano</i> , 2015 , 9, 5432-9	16.7	69
134	Characterization and Applications of New High Quality LuAG:Ce and LYSO:Ce fibers. <i>Journal of Physics: Conference Series</i> , 2015 , 587, 012067	0.3	1
133	Visible Photoluminescence in Cubic (3C) Silicon Carbide Coupled to High Quality Microdisk Resonators 2015 ,		1
132	Ge Addition during 4H-SiC Epitaxial Growth by CVD: Mechanism of Incorporation. <i>Materials Science Forum</i> , 2015 , 821-823, 115-120	0.4	
131	Behavior and Chemical Reactions of Liquid Si and Ge on Si _{1-x} C _x Surface. <i>Materials Science Forum</i> , 2015 , 821-823, 121-124	0.4	0
130	Understanding of the Growth Mechanism Leading to Twin Boundary Elimination during 3C-SiC Heteroepitaxy on SiC Substrate by CVD. <i>Materials Science Forum</i> , 2015 , 821-823, 209-212	0.4	1
129	Preliminary Study on the Effect of Micrometric Ge-Droplets on the Characteristics of Ni/4H-SiC Schottky Contacts. <i>Materials Science Forum</i> , 2015 , 821-823, 424-427	0.4	
128	A Study on the Chemistry of Epitaxial Ti ₃ SiC ₂ Formation on 4H-SiC Using Al-Ti Annealing. <i>Materials Science Forum</i> , 2015 , 821-823, 432-435	0.4	3
127	MOS Interface Characteristics of In Situ Ge-Doped 4H-SiC Homoepitaxial Layers. <i>Materials Science Forum</i> , 2015 , 821-823, 512-515	0.4	1
126	AlN hollow-nanofilaments by electrospinning. <i>Nanotechnology</i> , 2015 , 26, 085603	3.4	8
125	3C-SiC Heteroepitaxial Growth on Silicon: The Quest for Holy Grail. <i>Critical Reviews in Solid State and Materials Sciences</i> , 2015 , 40, 56-76	10.1	52
124	Visible Photoluminescence from Cubic (3C) Silicon Carbide Microdisks Coupled to High Quality Whispering Gallery Modes. <i>ACS Photonics</i> , 2015 , 2, 14-19	6.3	31

123	Development and Characterization of Inorganic Scintillating Fibers Made of LuAG:Ce and LYSO:Ce. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 353-361	1.7	4
122	Ge incorporation inside 4H-SiC during homoepitaxial growth by chemical vapor deposition. <i>Acta Materialia</i> , 2014 , 75, 219-226	8.4	11
121	Characterization and optimization of new high-quality inorganic fibers made of LuAG:Ce and LYSO:Ce 2014 ,		1
120	Applications of Vapor-Liquid-Solid Selective Epitaxy of Highly p-Type Doped 4H-SiC: PiN Diodes with Peripheral Protection and Improvement of Specific Contact Resistance of Ohmic Contacts. <i>Materials Science Forum</i> , 2014 , 778-780, 639-644	0.4	3
119	Characterization of Ge-Doped Homoepitaxial Layers Grown by Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2014 , 778-780, 261-264	0.4	7
118	Ge Assisted 3C-SiC Nucleation and Growth by Vapour Phase Epitaxy on On-Axis 4H-SiC Substrate. <i>Materials Science Forum</i> , 2014 , 806, 27-31	0.4	
117	Electrical Characteristics of Schottky Contacts on Ge-Doped 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 706-709	0.4	11
116	3C-SiC Seeded Growth on Diamond Substrate by VLS Transport. <i>Materials Science Forum</i> , 2014 , 778-780, 234-237	0.4	
115	Heteroepitaxy of P-Doped 3C-SiC on Diamond by VLS Transport. <i>Materials Science Forum</i> , 2014 , 806, 33-37	0.4	
114	Improvement of the Specific Contact Resistance on P-Type 4H-SiC by Using a Highly P-Typed Doped 4H-SiC Layer Selectively Grown by VLS Transport. <i>Materials Science Forum</i> , 2014 , 806, 57-60	0.4	
113	Ge Assisted SiC Epitaxial Growth by CVD on SiC Substrate. <i>Materials Science Forum</i> , 2014 , 778-780, 187-192		5
112	Heteroepitaxial CVD Growth of 3C-SiC on Diamond Substrate. <i>Materials Science Forum</i> , 2014 , 778-780, 226-229	0.4	1
111	Influence of Ga doping on the microstructure of 3C-SiC layers grown on 4H-SiC substrates by VLS mechanism. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 72-75		2
110	Photonic crystal cavities in cubic (3C) polytype silicon carbide films. <i>Optics Express</i> , 2013 , 21, 32623-9	3.3	50
109	Study of the Nucleation of p-Doped SiC in Selective Epitaxial Growth Using VLS Transport. <i>Materials Science Forum</i> , 2013 , 740-742, 177-180	0.4	1
108	p-Doped SiC Growth on Diamond Substrate by VLS Transport. <i>Materials Science Forum</i> , 2013 , 740-742, 331-334	0.4	3
107	Elaboration of Core Si/Shell SiC Nanowires. <i>Materials Science Forum</i> , 2013 , 740-742, 306-310	0.4	
106	Electrical Characterization of PiN Diodes with p+ Layer Selectively Grown by VLS Transport. <i>Materials Science Forum</i> , 2013 , 740-742, 911-914	0.4	7

105	Exploring SiC Growth Limitation of Vapor-Liquid-Solid Mechanism when Using Two Different Carbon Precursors. <i>Materials Science Forum</i> , 2013 , 740-742, 323-326	0.4	
104	Deposition of nanocrystalline translucent h-BN films by chemical vapor deposition at high temperature. <i>Thin Solid Films</i> , 2012 , 520, 2424-2428	2.2	12
103	Investigation of 3C-SiC growth on Si(111) by vapor-liquid-solid transport using a SiGe liquid phase. <i>Journal of Crystal Growth</i> , 2012 , 354, 119-128	1.6	3
102	Prism-coupled surface wave accelerator based on silicon carbide. <i>Physical Review Special Topics: Accelerators and Beams</i> , 2012 , 15,		6
101	Epitaxial Growth of 3C-SiC onto Silicon Substrate by VLS Transport Using CVD-Grown 3C-SiC Seeding Layer. <i>Materials Science Forum</i> , 2012 , 711, 35-39	0.4	
100	On Applicability of Time-Resolved Optical Techniques for Characterization of Differently Grown 3C-SiC Crystals and Heterostructures. <i>Materials Science Forum</i> , 2012 , 711, 159-163	0.4	1
99	Elimination of Twin Boundaries when Growing 3C-SiC Heteroepitaxial by Vapour-Liquid-Solid Mechanism on Patterned 4H-SiC Substrate. <i>Materials Science Forum</i> , 2012 , 711, 11-15	0.4	
98	Buried Selective Growth of p-Doped SiC by VLS Epitaxy. <i>Materials Science Forum</i> , 2012 , 717-720, 169-172	0.4	13
97	Seeding Layer Influence on the Low Temperature Photoluminescence Intensity of 3C-SiC Grown on 6H-SiC by Sublimation Epitaxy. <i>Materials Science Forum</i> , 2012 , 711, 149-153	0.4	2
96	Surface Morphology Evolution after Epitaxial Growth on 4 μ Off-Axis 4H-SiC Substrate. <i>Materials Science Forum</i> , 2012 , 717-720, 145-148	0.4	2
95	Study of the Lateral Growth by VLS Mechanism Using Al-Based Melts on Patterned Si Substrate. <i>Materials Science Forum</i> , 2012 , 717-720, 165-168	0.4	
94	From Si nanowire to SiC nanotube. <i>Journal of Nanoparticle Research</i> , 2011 , 13, 5425-5433	2.3	22
93	Growing 3C-SiC heteroepitaxial layers on SiC substrate by vapour-liquid-solid mechanism from the Al-Ce-Si ternary system. <i>Journal of Crystal Growth</i> , 2011 , 318, 397-400	1.6	3
92	On the Characterization of Boron in BGeAs Nano-Films Using IBA Techniques. <i>Advanced Materials Research</i> , 2011 , 324, 314-317	0.5	
91	Effect of nitrogen impurity on the stabilization of 3C-SiC polytype during heteroepitaxial growth by vapor-liquid-solid mechanism on 6H-SiC substrates. <i>Diamond and Related Materials</i> , 2011 , 20, 808-813	3.5	1
90	Growth of silicon oxide nanowires at low temperature using tin hydroxide catalyst. <i>Journal of Crystal Growth</i> , 2011 , 320, 55-62	1.6	9
89	Elaboration and characterization of boron doping during SiC growth by VLS mechanism. <i>Journal of Crystal Growth</i> , 2011 , 327, 46-51	1.6	2
88	Nanoscale probing of dielectric breakdown at SiO ₂ /3C-SiC interfaces. <i>Journal of Applied Physics</i> , 2011 , 109, 013707	2.5	7

87	Investigation of 3C-SiC Lateral Growth on 4H-SiC Mesas. <i>Materials Science Forum</i> , 2011 , 679-680, 111-114.	0.4	2
86	MOS Capacitors Fabricated on 3C-SiC(111) Layers Grown on 6H-SiC(0001). <i>Journal of the Electrochemical Society</i> , 2011 , 158, H630	3.9	6
85	Investigation of the Growth of 3C-SiC on Si by Vapor-Liquid-Solid (VLS) Transport. <i>Materials Science Forum</i> , 2011 , 679-680, 99-102	0.4	1
84	On the Quantification of Al Incorporated in SiC Material Using Particle Induced X-Ray Emission Technique. <i>Materials Science Forum</i> , 2011 , 679-680, 189-192	0.4	
83	New Approaches to In Situ Doping of SiC Epitaxial Layers. <i>Advanced Materials Research</i> , 2011 , 324, 14-19.	0.5	1
82	On the Characterization of Ultra Thin Al Films Deposited onto SiC Substrate Using PIXE Technique. <i>Advanced Materials Research</i> , 2011 , 324, 302-305	0.5	
81	3C-SiC MOS Based Devices: From Material Growth to Device Characterization. <i>Materials Science Forum</i> , 2011 , 679-680, 433-436	0.4	5
80	Nondestructive Evaluation of Photo-Electrical Properties of 3C-SiC (111) Homoepitaxial Layers Grown by CVD. <i>Materials Science Forum</i> , 2011 , 679-680, 153-156	0.4	1
79	On the Mechanism of Twin Boundary Elimination in 3C-SiC(111) Heteroepitaxial Layers on SiC Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 71-74	0.4	7
78	Structural and Optical Investigation of VLS Grown (111) 3C-SiC Layers on 6H-SiC Substrates in Sn-Based Melts. <i>Materials Science Forum</i> , 2011 , 679-680, 165-168	0.4	
77	Influence of Post-Growth Annealing on the Defects Nature and Distribution in VLS Grown (111) 3C-SiC Layers. <i>Materials Science Forum</i> , 2011 , 679-680, 241-244	0.4	2
76	Overview of 3C-SiC Crystalline Growth. <i>Materials Science Forum</i> , 2010 , 645-648, 49-54	0.4	12
75	Optical Characterization of VLS+CVD Grown 3C-SiC Films by Non-Linear and Photoluminescence Techniques. <i>Materials Science Forum</i> , 2010 , 645-648, 443-446	0.4	6
74	Properties of 3C-SiC Grown by Sublimation Epitaxy on Different Type of Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 183-186	0.4	2
73	TEM and LTPL Investigations of 3C-SiC Layers Grown by LPE on (100) and (111) 3C-SiC Seeds. <i>Materials Science Forum</i> , 2010 , 645-648, 383-386	0.4	1
72	Investigation of 3C-SiC(111) Homoepitaxial Growth by CVD at High Temperature. <i>Materials Science Forum</i> , 2010 , 645-648, 127-130	0.4	6
71	Further Evidence of Nitrogen Induced Stabilization of 3C-SiC Polytype during Growth from a Si-Ge Liquid Phase. <i>Materials Science Forum</i> , 2010 , 645-648, 163-166	0.4	3
70	Is the Liquid Phase a Viable Approach for Bulk Growth of 3C-SiC?. <i>Materials Science Forum</i> , 2010 , 645-648, 67-70	0.4	5

69	Low Doped 3C-SiC Layers Deposited by the Vapour-Liquid-Solid Mechanism on 6H-SiC Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 171-174	0.4	6
68	Reliability of Thin Thermally Grown SiO ₂ on 3C-SiC Studied by Scanning Probe Microscopy. <i>Materials Science Forum</i> , 2010 , 645-648, 833-836	0.4	1
67	LTPL Investigation of N-Ga and N-Al Donor-Acceptor Pair Spectra in 3C-SiC Layers Grown by VLS on 6H-SiC Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 415-418	0.4	2
66	Highly confined hybrid spoof surface plasmons in ultrathin metal-dielectric heterostructures. <i>Physical Review Letters</i> , 2010 , 105, 176803	7.4	24
65	Growth of Nanocrystalline Translucent h-BN Films Deposited by CVD at High Temperature on SiC Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 1191-1194	0.4	3
64	Influence of the C/Si Ratio on the Dopant Concentration and Defects in CVD Grown 3C-SiC Homoepitaxial Layers 2010 ,		3
63	Detailed study of the influence of surface misorientation on the density of Anti-Phase Boundaries in 3C-SiC layers grown on (001) silicon 2010 ,		6
62	Deep levels in hetero-epitaxial as-grown 3C-SiC 2010 ,		1
61	Defects in (111) 3C-SiC layers grown at different temperatures by VLS and CVD on 6H-SiC substrates 2010 ,		2
60	Midinfrared Index Sensing of pL-Scale Analytes Based on Surface Phonon Polaritons in Silicon Carbide <i>Journal of Physical Chemistry C</i> , 2010 , 114, 7489-7491	3.8	39
59	Measurements of the negative refractive index of sub-diffraction waves propagating in an indefinite permittivity medium. <i>Optics Express</i> , 2010 , 18, 22734-46	3.3	30
58	Sublimation Growth and Structural Characterization of 3C-SiC on Hexagonal and Cubic SiC Seeds. <i>Materials Science Forum</i> , 2010 , 645-648, 175-178	0.4	16
57	Incorporation of group III, IV and V elements in 3C-SiC(111) layers grown by the vapour-liquid-solid mechanism. <i>Journal of Crystal Growth</i> , 2010 , 312, 3443-3450	1.6	8
56	Evolution of 3C-SiC islands nucleated from a liquid phase on Si face SiC substrates. <i>Thin Solid Films</i> , 2010 , 518, 4234-4241	2.2	5
55	Improved Ni/3C-SiC contacts by effective contact area and conductivity increases at the nanoscale. <i>Applied Physics Letters</i> , 2009 , 94, 112104	3.4	16
54	Searching for Ge Clusters inside 3C-SiC Layers Grown by Vapor-Liquid-Solid Mechanism on 6H-SiC Substrates. <i>Materials Science Forum</i> , 2009 , 615-617, 185-188	0.4	8
53	Nano-Electro-Structural Evolution of Ni-Si Ohmic Contacts to 3C-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 569-572	0.4	
52	Effects of Temperature and Heating Rate on the Precipitation of 3C-SiC Islands on 4H-SiC(0001) from a Liquid Phase. <i>Materials Science Forum</i> , 2009 , 615-617, 193-196	0.4	

51	Defect-induced polytype transformations in LPE grown SiC epilayers on (1 1 1) 3C-SiC seeds grown by VLS on 6H-SiC. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4727-4730	2.8	1
50	Study of the 3C-SiC nucleation from a liquid phase on a C face 6H-SiC substrate. <i>Journal of Crystal Growth</i> , 2009 , 311, 2385-2390	1.6	16
49	Critically coupled surface phonon-polariton excitation in silicon carbide. <i>Optics Letters</i> , 2009 , 34, 2667-9	3	45
48	Vapor-Liquid-Solid Growth of 3C-SiC on SiC Substrates. 1. Growth Mechanism. <i>Crystal Growth and Design</i> , 2008 , 8, 1044-1050	3.5	38
47	Vapor-Liquid-Solid Growth of 3C-SiC on SiC Substrates. 2. Growth Kinetics. <i>Crystal Growth and Design</i> , 2008 , 8, 1051-1054	3.5	15
46	Optical Study of Ge Incorporation in Cubic SiC Layers Grown by VLS. <i>Materials Science Forum</i> , 2008 , 600-603, 529-532	0.4	6
45	Nucleation of 3C-SiC on 6H-SiC from a liquid phase. <i>Acta Materialia</i> , 2007 , 55, 6873-6880	8.4	24
44	Growth of SiC from a Liquid Phase at Low Temperature. <i>Materials Science Forum</i> , 2007 , 556-557, 41-46	0.4	6
43	How to Grow 3C-SiC Single Domain on SiC(0001) by Vapor-Liquid-Solid Mechanism. <i>Materials Science Forum</i> , 2007 , 556-557, 187-190	0.4	3
42	Boron Doping during Vapor-Liquid-Solid Growth of Homoepitaxial 4H-SiC Layers. <i>Materials Science Forum</i> , 2007 , 556-557, 65-68	0.4	4
41	Optical Investigation of Cubic SiC Layers Grown on Hexagonal SiC Substrates by CVD and VLS. <i>Materials Science Forum</i> , 2007 , 556-557, 403-406	0.4	8
40	Strain Tailoring in 3C-SiC Heteroepitaxial Layers Grown on Si(100). <i>Chemical Vapor Deposition</i> , 2006 , 12, 483-488		35
39	A Vapor-Liquid-Solid Mechanism for Growing 3C-SiC Single-Domain Layers on 6H-SiC(0001). <i>Advanced Functional Materials</i> , 2006 , 16, 975-979	15.6	77
38	Very Low Interface State Density From Thermally Oxidized Single-Domain 3C-SiC/6H-SiC Grown by Vapour-Liquid-Solid Mechanism. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 6823-6829	1.4	18
37	Single-Domain 3C-SiC Epitaxially Grown on 6H-SiC by the VLS Mechanism. <i>Materials Science Forum</i> , 2006 , 527-529, 287-290	0.4	6
36	Effect of the Crystallization Conditions on the Epitaxial Relationship of Si Deposited on 3C-SiC(100). <i>Materials Science Forum</i> , 2006 , 527-529, 1563-1566	0.4	3
35	Using Vapour-Liquid-Solid Mechanism for SiC Homoepitaxial Growth on on-axis SiC (0001) at Low Temperature. <i>Materials Science Forum</i> , 2006 , 527-529, 271-274	0.4	1
34	Characterization of a 3C-SiC Single Domain Grown on 6H-SiC(0001) by a Vapor-Liquid-Solid Mechanism. <i>Crystal Growth and Design</i> , 2006 , 6, 2598-2602	3.5	27

33	Probing the effect of temperature on the incorporation of Al species in a SiC matrix. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1265-1268		7
32	Analysis of SiC Islands Formation during First Steps of Si Carbonization Process. <i>Materials Science Forum</i> , 2005 , 483-485, 555-558	0.4	2
31	Microstructural Characterization of 3C-SiC Thin Films Grown by Flash Lamp Induced Liquid Phase Epitaxy. <i>Materials Science Forum</i> , 2005 , 483-485, 295-298	0.4	5
30	Planar Defects, Voids and their Relationship in 3C-SiC Layers. <i>Materials Science Forum</i> , 2005 , 483-485, 189-192	0.4	
29	Is the Al Solubility Limit in SiC Temperature Dependent or not?. <i>Materials Science Forum</i> , 2005 , 483-485, 125-128	0.4	4
28	Electrical Characterisation of Heavily Al Doped 4H-SiC Layer Grown by Vapour-Liquid-Solid Epitaxy in Al-Si Melt. <i>Materials Science Forum</i> , 2005 , 483-485, 421-424	0.4	4
27	Comparative Evaluation of Free-Standing 3C-SiC Crystals. <i>Materials Science Forum</i> , 2005 , 483-485, 229-232	0.4	5
26	Growth and Characterisation of Heavily Al-Doped 4H-SiC Layers Grown by VLS in an Al-Si Melt. <i>Materials Science Forum</i> , 2004 , 457-460, 735-738	0.4	8
25	Flash Lamp Supported Deposition of 3C-SiC (FLASiC) is a Promising Technique to Produce High Quality Cubic SiC Layers. <i>Materials Science Forum</i> , 2004 , 457-460, 175-180	0.4	14
24	Checker-Board Carbonization for Control and Reduction of the Mean Curvature of 3C-SiC Layers Grown on Si(100) Substrates. <i>Materials Science Forum</i> , 2004 , 457-460, 265-268	0.4	5
23	Interfacial Strain and Defects in Si (001) Carbonization Layers for 3C-SiC Hetero-Epitaxy. <i>Materials Science Forum</i> , 2004 , 457-460, 277-280	0.4	3
22	Control of the 2D/3D Transition of Cubic GaN/AlN Nanostructures on 3C-SiC Epilayers. <i>Materials Science Forum</i> , 2004 , 457-460, 1561-1564	0.4	1
21	Investigation of Thick 3C-SiC Films Re-Grown on Thin 35 nm "Flash Lamp Annealed" 3C-SiC Layers. <i>Materials Science Forum</i> , 2004 , 457-460, 313-316	0.4	5
20	Potential of HMDS/C3H8 Precursor System for the Growth of State of the Art Heteroepitaxial 3C-SiC Layers on Si(100). <i>Materials Science Forum</i> , 2004 , 457-460, 281-284	0.4	
19	Comparison of Different Metal Additives to Si for the Homoepitaxial Growth of 4H-SiC Layers by Vapour-Liquid-Solid Mechanism. <i>Materials Science Forum</i> , 2004 , 457-460, 245-248	0.4	1
18	Formation of 3C-SiC Films Embedded in SiO ₂ by Sacrificial Oxidation. <i>Materials Science Forum</i> , 2004 , 457-460, 1515-1518	0.4	2
17	Structural Characterization of Thin 3C-SiC Films Annealed by the Flash Lamp Process. <i>Materials Science Forum</i> , 2004 , 457-460, 351-354	0.4	4
16	Growth by a vapour-liquid-solid mechanism: a new approach for silicon carbide epitaxy. <i>New Journal of Chemistry</i> , 2004 , 28, 889-896	3.6	52

15	On the growth of 4H-SiC by low-temperature liquid phase epitaxy in Al rich AlSi melts. <i>Journal of Crystal Growth</i> , 2003 , 254, 123-130	1.6	26
14	Nature effect of the gas during high temperature treatments of 4H-SiC substrates. <i>Applied Surface Science</i> , 2003 , 207, 200-207	6.7	5
13	SiC Homoepitaxial Growth at Low Temperature by Vapor-Liquid-Solid Mechanism in AlSi Melt. <i>Crystal Growth and Design</i> , 2003 , 3, 285-287	3.5	11
12	A comprehensive study of SiC growth processes in a VPE reactor. <i>Thin Solid Films</i> , 2002 , 402, 83-89	2.2	43
11	Direct synthesis of β -SiC and h-BN coated β -SiC nanowires. <i>Solid State Communications</i> , 2002 , 124, 157-161	1.6	38
10	Effect of the Si Droplet Size on the VLS Growth Mechanism of SiC Homoepitaxial Layers. <i>Materials Science Forum</i> , 2002 , 389-393, 287-290	0.4	10
9	SiO ₂ as Oxygen Source for the Chemical Vapor Transport of SiC. <i>Materials Science Forum</i> , 2002 , 389-393, 307-310	0.4	2
8	Improved SiCOI Structures Elaborated by Heteroepitaxy of 3C-SiC on SOI. <i>Materials Science Forum</i> , 2002 , 389-393, 343-346	0.4	8
7	How to Grow Unstrained 3C-SiC Heteroepitaxial Layers on Si (100) Substrates. <i>Materials Science Forum</i> , 2001 , 353-356, 155-158	0.4	21
6	Aluminium-Silicon as a Melt for the Low Temperature Growth of SiC Crystals. <i>Materials Science Forum</i> , 2001 , 353-356, 85-90	0.4	9
5	Growth mode of AlN epitaxial layers on 6H-SiC by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2000 , 209, 415-418	1.6	13
4	RHEED monitoring of AlN epitaxial growth by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2000 , 210, 429-434	1.6	16
3	Growth Mode and Kinetics of Atmospheric Pressure Chemical Vapour Deposition of β -SiC on Si(100) Substrate. <i>Materials Science Forum</i> , 1998 , 264-268, 227-230	0.4	9
2	Growth and doping of silicon carbide with germanium: a review. <i>Critical Reviews in Solid State and Materials Sciences</i> , 1-18	10.1	1
1	Liquid Si-Induced 4H-SiC Surface Structuring Using a Sandwich Configuration. <i>Materials Science Forum</i> , 1062, 8-12	0.4	